

R2J20655BNP

Integrated Driver - MOS FET (DrMOS)

R07DS0548EJ0101 (Previous No.: R07DS0540EJ0100) Rev.1.01 Sep 30, 2011

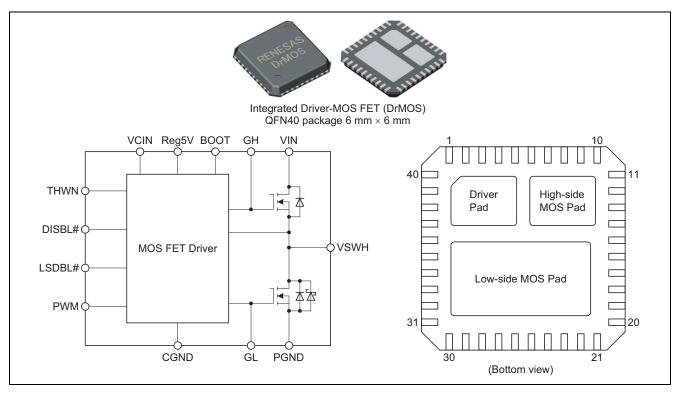
Description

The R2J20655BNP multi-chip module incorporates a high-side MOS FET, low-side MOS FET, and MOS-FET driver in a single QFN package. The on and off timing of the power MOS FET is optimized by the built-in driver, making this device suitable for large-current buck converters. The chip also incorporates a high-side bootstrap switch, eliminating the need for an external SBD for this purpose.

Features

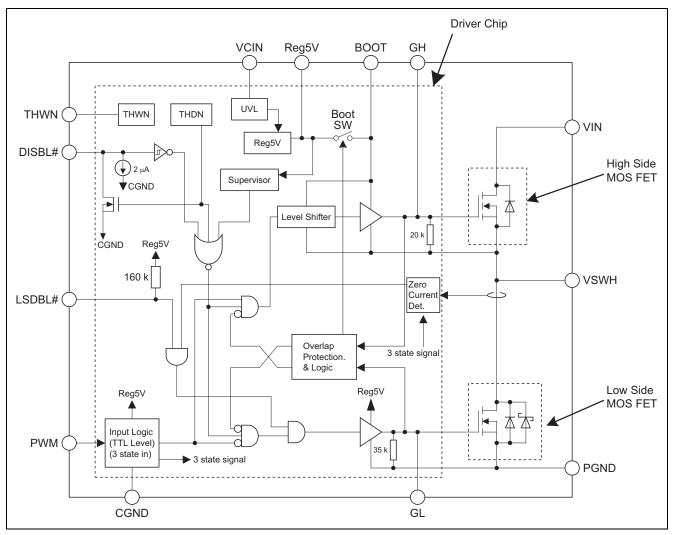
- Based on Intel 6×6 DrMOS Specification.
- Built-in power MOS FET suitable for Desktop, Server application.
- Low-side MOS FET with built-in SBD for lower loss and reduced ringing.
- Built-in driver circuit which matches the power MOS FET
- Built-in tri-state input function which can support a number of PWM controllers
- High-frequency operation (above 1 MHz) possible
- VIN operating-voltage range: 27 Vmax
- Large average output current (Max.35 A)
- Achieve low power dissipation
- Controllable driver: Remote on/off
- Support Mid-Voltage PWM signal to enter zero current detection
- Double thermal protection: Thermal Warning & Thermal Shutdown
- Built-in bootstrapping Switch
- Small package: QFN40 (6 mm × 6 mm × 0.95 mm)
- Pb-free/Halogen-Free

Outline





Block Diagram



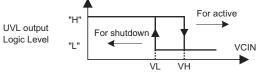
Notes: 1. Truth table for the DISBL# pin

DISBL# Input	Driver Chip Status		
"L"	Shutdown (GL, GH = "L")		
"Open"	Shutdown (GL, GH = "L")		
"H"	Enable (GL, GH = "Active")		

2. Truth table for the LSDBL# pin & PWM pin

LSDBL#	PWM	
Input	Input	GL Status
"L"	*	"L"
"Open"	"L" or "H"	"Continuous
or "H"		Conduction Mode"
	"Open"	"Zero Current
	or "Mid"	Detection" Mode

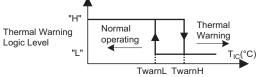
3. Output signal from the UVL block



5. Truth table for the THDN block

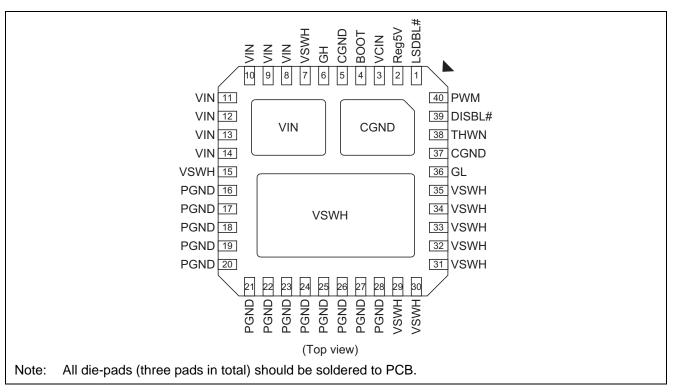
Driver IC Temp.	Driver Chip Status
< 150°C	Enable (GL, GH = "Active")
> 150°C	Shutdown (GL, GH = "L") (latch-off)

4. Output signal from the THWN block





Pin Arrangement



Pin Description

Pin Name	Pin No.	Description	Remarks
LSDBL#	1	Low-side gate disable	When asserted "L" signal, Low-side gate disable
Reg5V	2	+5 V logic power supply output	
VCIN	3	Control input voltage	Driver Vcc input
BOOT	4	Bootstrap voltage pin	To be supplied +5 V through internal switch
CGND	5, 37, Pad	Control signal ground	Should be connected to PGND externally
GH	6	High-side gate signal	Pin for monitor
VIN	8 to 14, Pad	Input voltage	
VSWH	7, 15, 29 to 35, Pad	Phase output/Switch output	
PGND	16 to 28	Power ground	
GL	36	Low-side gate signal	Pin for monitor
THWN	38	Thermal warning	Thermal warning when over 115°C
DISBL#	39	Signal disable	Disabled when DISBL# is "L".
			This Pin is pulled low when internal IC over the
			thermal shutdown level, 150°C.
PWM	40	PWM drive logic input	5 V logic input



Absolute Maximum Ratings

				$(Ta = 25^{\circ}C)$
Item	Symbol	Rating	Units	Note
Power dissipation	Pt(25)	25	W	1
	Pt(110)	8		
Average output current	lout	35	А	
Input voltage	VIN(DC)	-0.3 to +27	V	2
	VIN(AC)	30		2, 4, 6
Switch node voltage	VSWH(DC)	27	V	2
	VSWH(AC)	30		2, 4, 6
BOOT voltage	VBOOT(DC)	32	V	2
	VBOOT(AC)	36		2, 4, 6
Supply voltage	VCIN	-0.3 to +27	V	2
PWM voltage	Vpwm	-0.3 to +5.5 @UVL OFF	V	2, 4
		-0.3 to +0.3 @UVL ON		2, 5
		-0.3 to Reg5V + 0.3		2, 7, 8
Other I/O voltage	Vdisbl, Vlsdbl	-0.3 to VCIN + 0.3	V	2
Reg5V voltage	Vreg5V	-0.3 to +6	V	2, 7
Reg5V current	Ireg5V	-20 to +0.1	mA	3
THWN/THDN current	Ithwn, Idisbl	0 to 1.0	mA	3
Operating junction temperature	Tj-opr	-40 to +150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. Pt(25) represents a PCB temperature of 25°C, and Pt(110) represents 110°C.

2. Rated voltages are relative to voltages on the CGND and PGND pins.

3. For rated current, (+) indicates inflow to the chip and (-) indicates outflow.

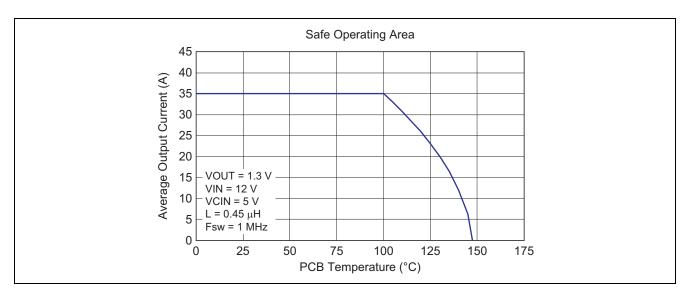
4. This rating is when UVL (Under Voltage Lock out) is ineffective (normal operation mode).

5. This rating is when UVL (Under Voltage Lock out) is effective (lock out mode).

6. The specification values indicated "AC" are limited within 10 ns.

7. This rating is when the external power-source is applied to Reg5V pin.

8. Reg5V + 0.3 V < 6 V



Item	Symbol	Rating	Units	Note
Input voltage	VIN	4.5 to 22	V	When the usage of VCIN = 4.5 V to 5.5 V,
Supply voltage & Drive voltage	VCIN	4.5 to 5.5 or 8 to 22	V	VCIN should be connected to Reg5V (Refer to "Pin Connection")

Recommended Operating Condition

Electrical Characteristics

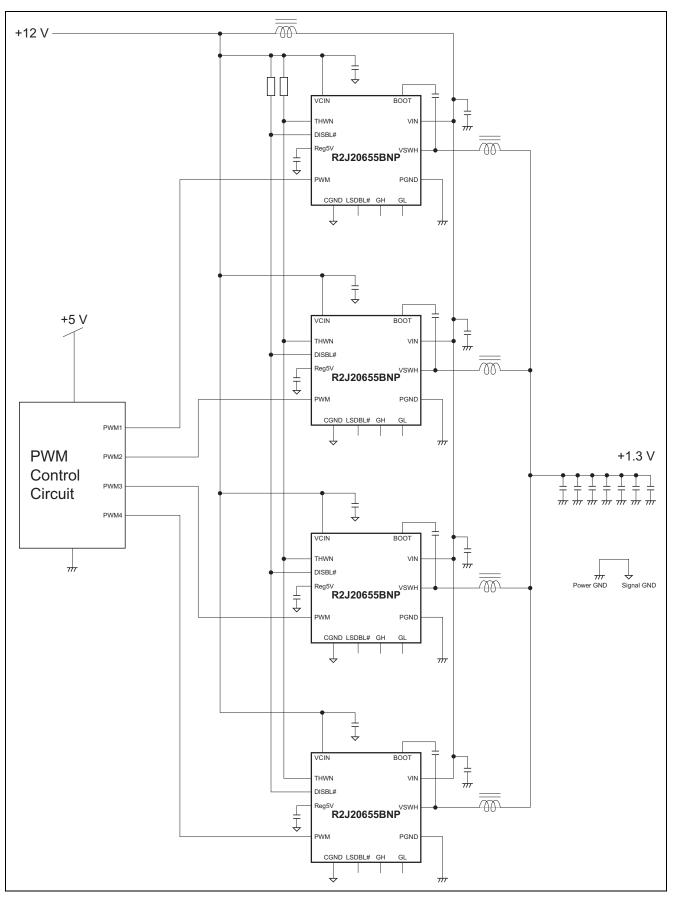
		(Ta	= 25°C, V	VCIN = 1	2 V, VSV	VH = 0 V	/, unless otherwise specified)
	ltem	Symbol	Min	Тур	Max	Units	Test Conditions
Supply	VCIN start threshold	V _H	7.0	7.4	7.8	V	
	VCIN shutdown threshold	VL	6.6	7.0	7.4	V	
	UVLO hysteresis	dUVL	_	0.4		V	$V_H - V_L$
	VCIN operating current	I _{CIN}	—	49	—	mA	f _{PWM} = 1 MHz, Ton_pwm = 120 ns
	VCIN disable current	I _{CIN-DISBL}	—		1.2	mA	DISBL# = 0 V, PWM = LSDBL# = Open
PWM	PWM input high level	V _{H-PWM}	4.1	_		V	5.0 V PWM interface
input	PWM input low level	V _{L-PWM}	_	_	0.8	V	
	PWM input resistance	R _{IN-PWM}	3.5	7.5	15	kΩ	$\frac{4V-1V}{I_{PWM}(V_{PWM=4V})-I_{PWM}(V_{PWM=1V})}$
	PWM input tri-state range	V _{IN-tri}	1.4		3.3	V	5.0 V PWM interface
DISBL#	Enable level	V _{ENBL}	2.0	_		V	
input	Disable level	V _{DISBL}	_	_	0.8	V	
	Input current	I _{DISBL}	_	2.0	5.0	μA	DISBL# = 1 V
	THDN on resistance	R _{THDN} * ¹	0.2	0.5	1.0	kΩ	DISBL# = 0.2 V
LSDBL#	Low-side activation level	V _{LSDBLH}	2.0	_		V	
input	Low-side disable level	V _{LSDBLL}	_	_	0.8	V	
	Input current	I _{LSDBL}	-52	-26	-12	μΑ	LSDBL# = 1 V
Thermal	Warning temperature	T _{THWN} * ¹	100	115	130	°C	Driver IC temperature
warning	Temperature hysteresis	T _{HYS} * ¹	—	15	—	°C	
	THWN on resistance	R _{THWN} * ¹	0.2	0.5	1.0	kΩ	THWN = 0.2 V
	THWN leakage current	I _{LEAK}	—	_	1.0	μΑ	THWN = 5 V
Thermal shutdown	Shutdown temperature	Tstdn *1	130	150	—	°C	Driver IC temperature
5 V	Output voltage	Vreg	4.95	5.2	5.45	V	
regulator	Line regulation	Vreg-line	-10	0	10	mV	VCIN = 12 V to 16 V
	Load regulation	Vreg-load	-10	0	10	mV	Ireg = 0 to 10 mA

Note: 1. Reference values for design. Not 100% tested in production.



Typical Application

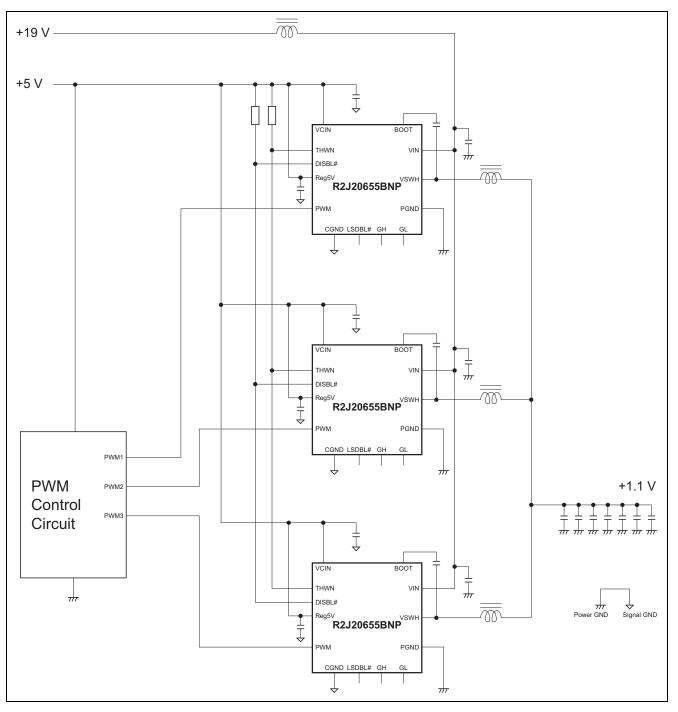
(1) Desktop/Server Application





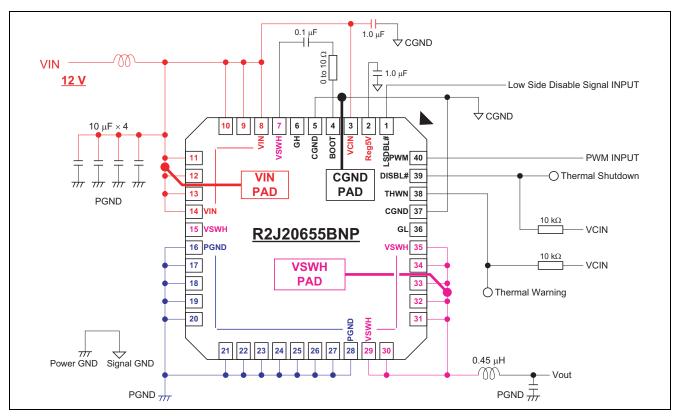
Typical Application (cont.)

(2) Notebook Application

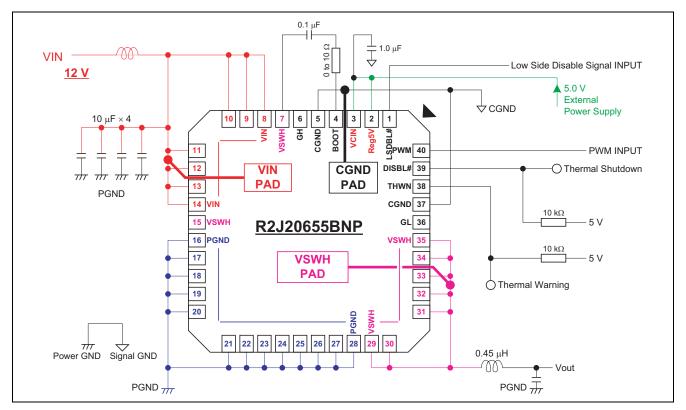


Pin Connection

(1) Single 12 V Application

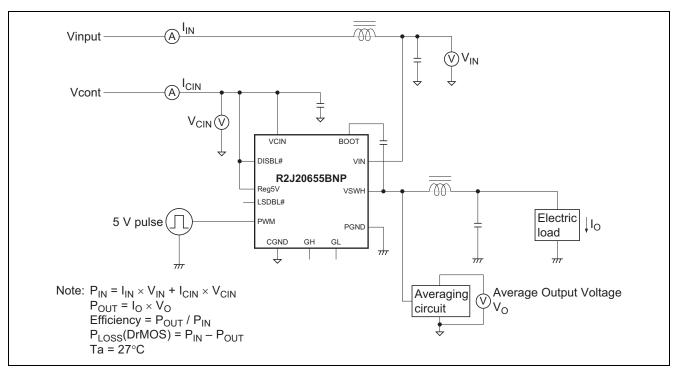


(2) VCIN 5 V Application



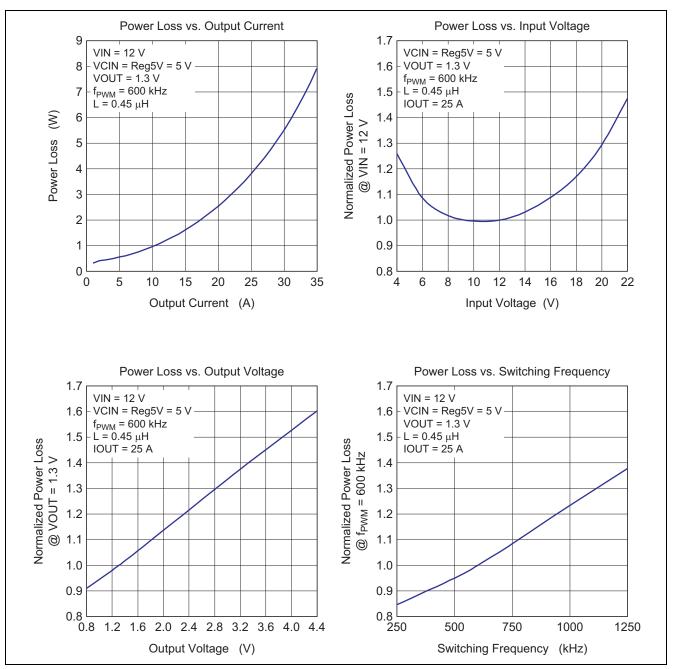


Test Circuit

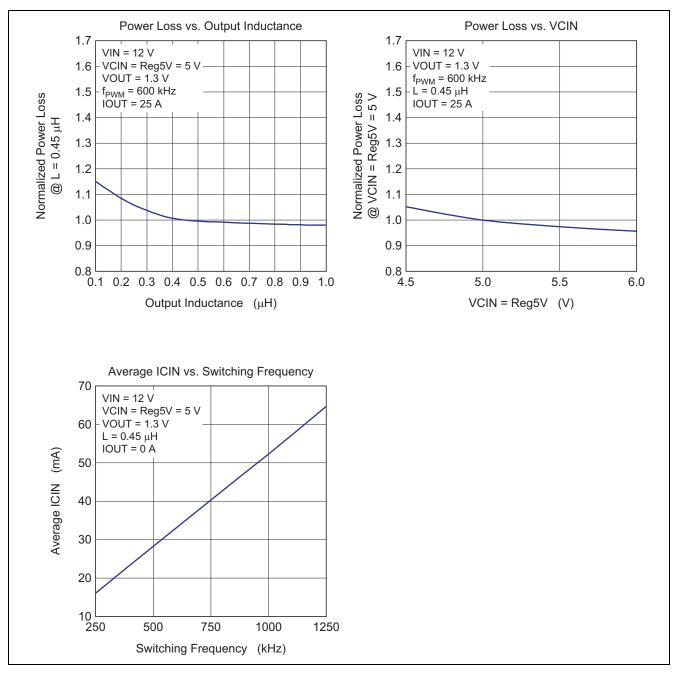




Typical Data



Typical Data (cont.)



Description of Operation

The DrMOS multi-chip module incorporates a high-side MOS FET, low-side MOS FET, and MOS-FET driver in a single QFN package. Since the parasitic inductance between each chip is extremely small, the module is highly suitable for use in buck converters to be operated at high frequencies. The control timing between the high-side MOS FET, low-side MOS FET, and driver is optimized so that high efficiency can be obtained at low output-voltage.

VCIN & DISBL#

The VCIN pin is connected to the UVL (under-voltage lockout) module, so that the built-in 5 V regulator is disabled as long as VCIN is 7.4 V or less. On cancellation of UVL, the built-in 5 V regulator remains enabled until the UVL input is driven to 7.0 V or less.

The built-in 5 V regulator is a series regulator with temperature compensation. A ceramic capacitor with a value of 0.1 μ F or more must be connected between the CGND plane and the Reg5V pin.

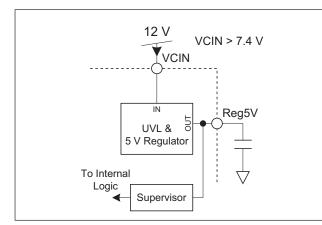
The output of 5 V regulator is monitored by the internal Supervisor circuits. When the Supervisor detects this output is more than 4.3 V (typ.), the driver state becomes active (figure 1.1). Supervisor circuit has hysteresis and its shutdown level of Supervisor is 3.8 V (typ.).

Figure 1.2 shows the application when the external 5 V regulator is used. When the Reg5V pin is applied into external 5 V, the Supervisor can activate the driver. In this application usage, VCIN should be connected to Reg5V.

The signal on pin DISBL# also enables or disables the circuit. When UVL disables the circuit, the built-in 5 V regulator does not operate, but when the signal on DISBL# disables the circuit, only output-pulse generation is terminated, and the 5 V regulator is not disabled.

Voltages from -0.3 V to VCIN+0.3 V can be applied to the DISBL# pin, so on/off control by a logic IC or the use of a resistor, etc., to pull the DISBL# line up to VCIN are both possible.

VCIN	DISBL#	REG5V	Driver State
L	*	0	Disable (GL, GH = L)
Н	L	Active	Disable (GL, GH = L)
Н	Н	Active	Active
н	Open	Active	Disable (GL, GH = L)





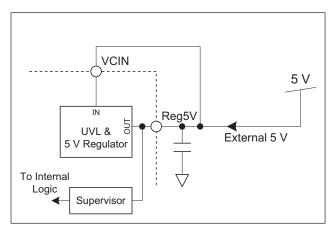


Figure 1.2 External 5 V Application



PWM & LSDBL#

The PWM pin is the signal input pin for the driver chip. When the PWM input is high, the gate of the high-side MOS FET (GH) is high and the gate of the low-side MOS FET (GL) is low.

When the PWM input becomes middle voltage or high impedance, Zero Current Detection (ZCD) function works. Figure 2 shows the operation diagram of PWM input and inductor current (IL).

PWM	GH	GL	IL
L	L	Н	*
Н	Н	L	*
Middle	L	Н	> 0
or	L	L	≤ 0
or Open			

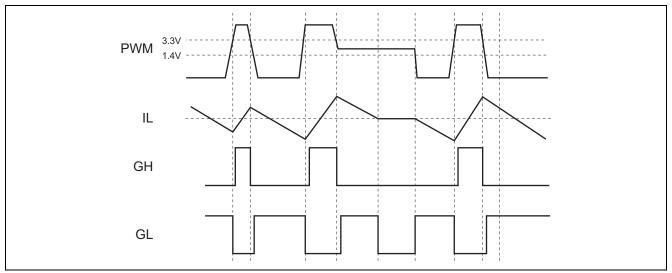


Figure 2 ZCD Operation Diagram

The equivalent circuit for the PWM-pin input is shown in the next figure. PWM SW is in the ON state during normal operation; if DISBL#-pin input is Low or Open State, the PWM SW is turned off.

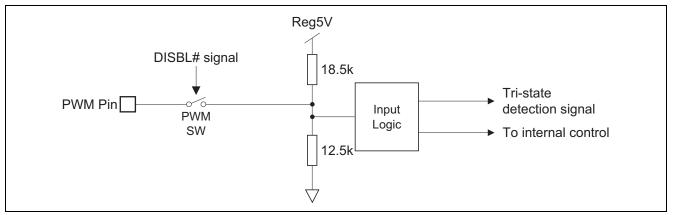


Figure 3 Equivalent Circuit for the PWM-pin Input

The LSDBL# pin is the Low Side Gate Disable pin for "Discontinuous Conduction Mode (DCM)" when LSDBL# is low.

This pin is internally pulled up to Reg5V with 160 k Ω resistor.

When low side disable function is not used, keep this pin open or pulled up to VCIN.

Truth Table for the LSDBL# pin & PWM pin

LSDBL# Input	PWM Input	GL Status
"L"	*	"L"
"Open" or "H"	"L" or "H"	"Continuous Conduction Mode"
	"Open" or "Mid"	"Zero Current Detection" Mode



THWN & THDN

This device has two level thermal detection, one is thermal warning and the other is thermal shutdown function.

This Thermal Warning feature is the indication of the high temperature status.

THWN is an open drain logic output signal and need to connect a pull-up resistor (ex.51 k Ω) to THWN for Systems with the thermal warning implementation.

When the chip temperature of the internal driver IC becomes over 115°C, Thermal warning function operates.

This signal is only indication for the system controller and does not disable DrMOS operation. When thermal warning function is not used, keep this pin open.

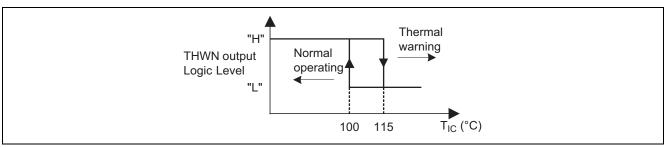


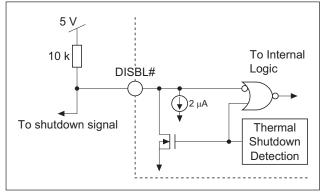
Figure 4 THWN Trigger Temperature

THDN is an internal thermal shutdown signal when driver IC becomes over 150°C.

This function makes High Side MOS FET and Low Side MOS FET turn off for the device protection from abnormal high temperature situation and at the same time DISBL# pin is pulled low internally to give notice to the system controller. Once thermal shutdown function operates, driver IC keeps DISBL# pin pulled low until VCIN becomes under UVL level (or under supervisor shutdown level).

Figure 5 shows the example of two types of DISBL# connection with the system controller signal.

Driver IC Temp.	Driver Chip Status
< 150°C	Enable (GL, GH = "Active")
> 150°C	Shutdown (GL, GH = "L")



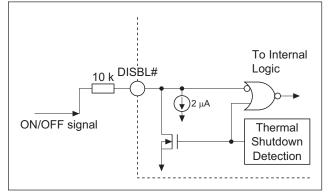


Figure 5.1 THDN Signal to the System Controller

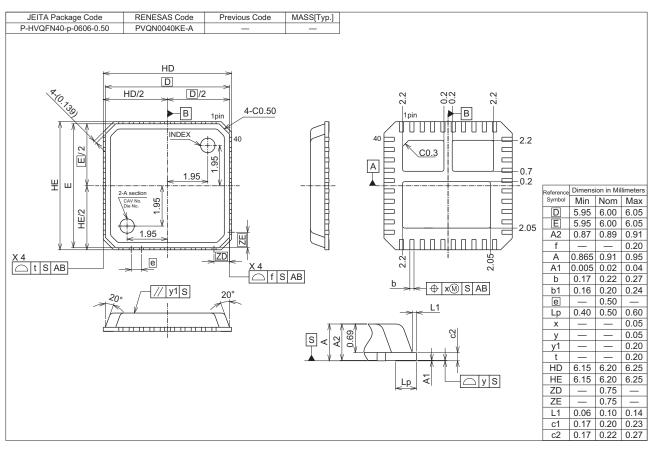
Figure 5.2 ON/OFF Signal from the System Controller

MOS FET

The MOS FETs incorporated in R2J20655BNP are highly suitable for synchronous-rectification buck conversion. For the high-side MOS FET, the drain is connected to the VIN pin and the source is connected to the VSWH pin. For the low-side MOS FET, the drain is connected to the VSWH pin and the source is connected to the PGND pin.



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
R2J20655BNP#G0	2500 pcs	Taping Reel



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